

# PolarHV™ Power MOSFET

## IXTP 1R6N50P IXTY 1R6N50P

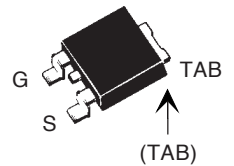
$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D25} &= 1.6 \text{ A} \\ R_{DS(on)} &\leq 6.5 \text{ } \Omega \end{aligned}$$

N-Channel Enhancement Mode

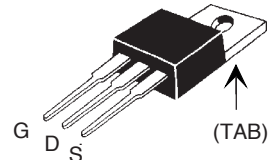

[www.DataSheet4U.com](http://www.DataSheet4U.com)

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	500	V
$V_{GS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	1.6	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	2.5	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	1.6	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	5	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	75	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 50 \text{ } \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	43	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10s Maximum tab temperature for soldering TO-252 package for 10s	300 260	$^\circ\text{C}$ $^\circ\text{C}$
$M_d$	Mounting torque (TO-220)	1.13/10	Nm/lb.in.
Weight	TO-252	0.8	g
	TO-220	4	g

TO-252 (IXTY)



TO-220 (IXTP)



G = Gate      D = Drain  
S = Source      TAB = Drain

### Features

- International standard packages
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

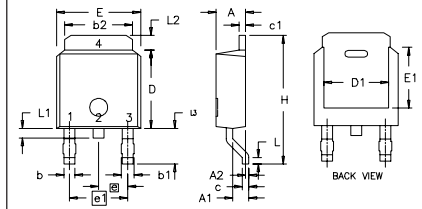
### Advantages

- Easy to mount
- Space savings
- High power density

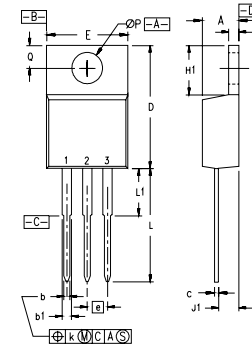
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ } \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ } \mu\text{A}$	3.0		5.5 V
$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$			5 $\mu\text{A}$
	$V_{GS} = 0 \text{ V}$			50 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \text{ } \mu\text{s}$ , duty cycle $d \leq 2 \%$			6.5 $\Omega$

Symbol	Test Conditions	Characteristic Values		
		$(T_j = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}, \text{ pulse test}$	0.7	1.4	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		140	pF
$C_{oss}$			20	pF
$C_{rss}$			2.6	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 20\ \Omega \text{ (External)}$		10	ns
$t_r$			16	ns
$t_{d(off)}$			25	ns
$t_f$			16	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		3.9	nC
$Q_{gs}$			1.4	nC
$Q_{gd}$			1.3	nC
$R_{thJC}$				2.9 K/W

Symbol	Test Conditions	Characteristic Values		
		$(T_j = 25^\circ\text{C}, \text{ unless otherwise specified})$		
		Min.	typ.	Max.
$I_s$	$V_{GS} = 0\text{ V}$			1.6 A
$I_{SM}$	Repetitive			2.5 A
$V_{SD}$	$I_F = I_s, V_{GS} = 0\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s}, \text{ duty cycle } d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 1.6\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$		400	ns

**TO-252 AA Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.19	2.38	0.086	0.094
A1	0.89	1.14	0.035	0.045
A2	0	0.13	0	0.005
b	0.64	0.89	0.025	0.035
b1	0.76	1.14	0.030	0.045
b2	5.21	5.46	0.205	0.215
c	0.46	0.58	0.018	0.023
c1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
D1	4.32	5.21	0.170	0.205
E	6.35	6.73	0.250	0.265
E1	4.32	5.21	0.170	0.205
e	2.28 BSC		0.090 BSC	
et	4.57 BSC		0.180 BSC	
H	9.40	10.42	0.370	0.410
L	0.51	1.02	0.020	0.040
L1	0.64	1.02	0.025	0.040
L2	0.89	1.27	0.035	0.050
L3	2.54	2.92	0.100	0.115

**TO-220 Outline**


Pins: 1 - Gate      2 - Drain

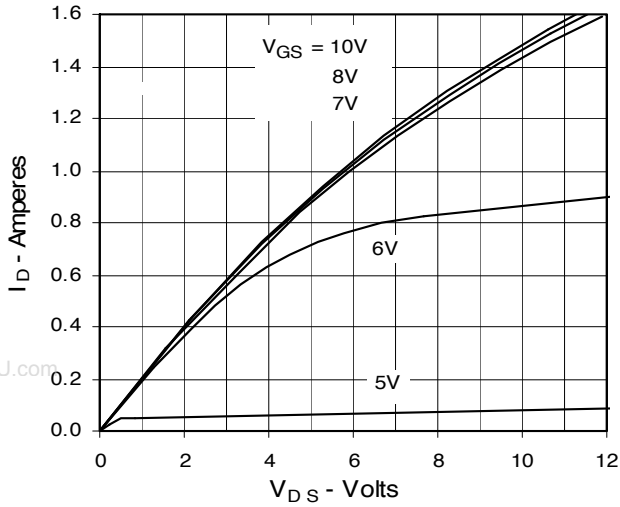
SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

IXYS reserves the right to change limits, test conditions, and dimensions.

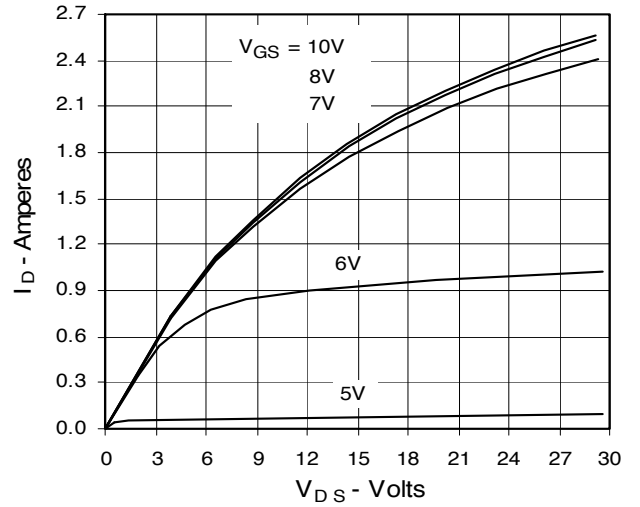
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505

6,683,344	6,727,585
6,710,405 B2	6,759,692
6,710,463	

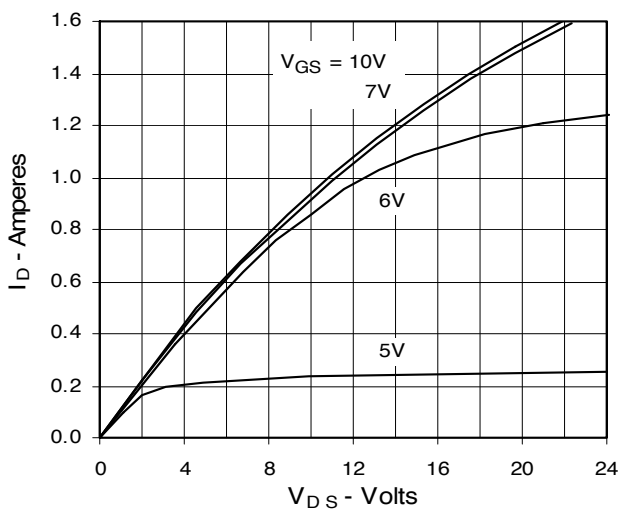
**Fig. 1. Output Characteristics**  
@ 25°C



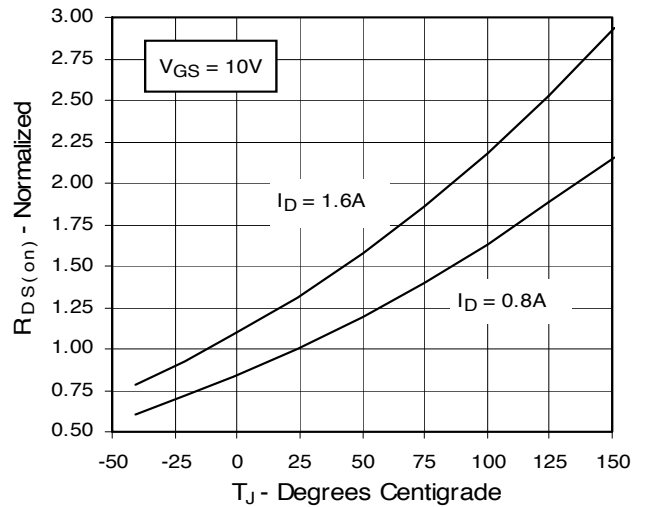
**Fig. 2. Extended Output Characteristics**  
@ 25°C



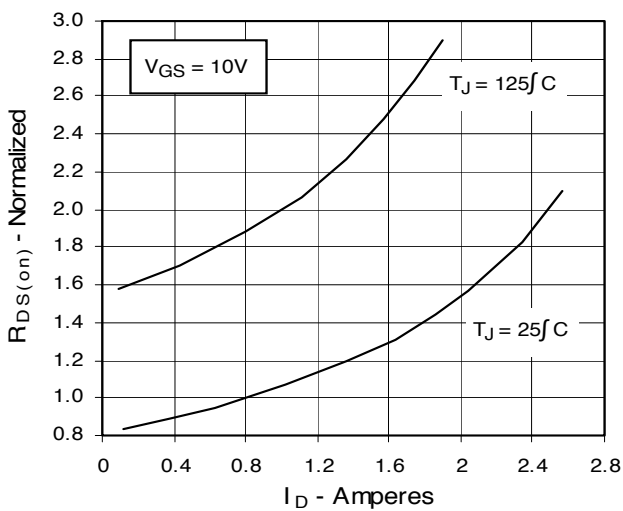
**Fig. 3. Output Characteristics**  
@ 125°C



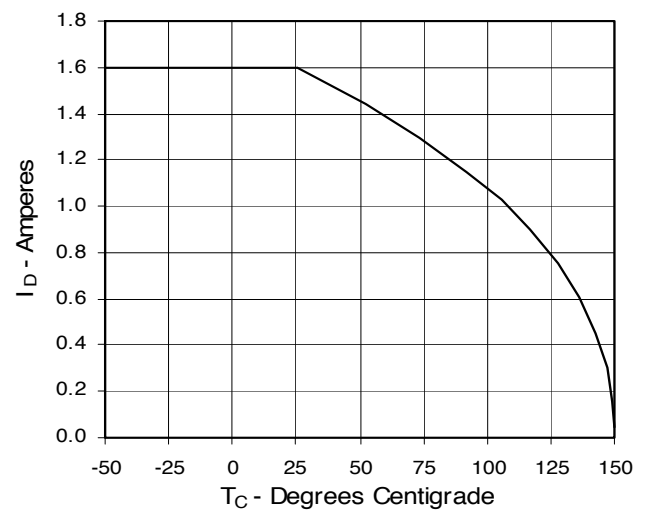
**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs. Junction Temperature**



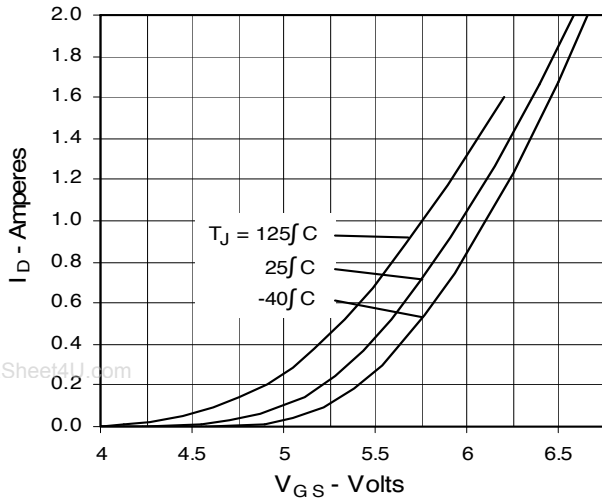
**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$  Value vs.  $I_D$**



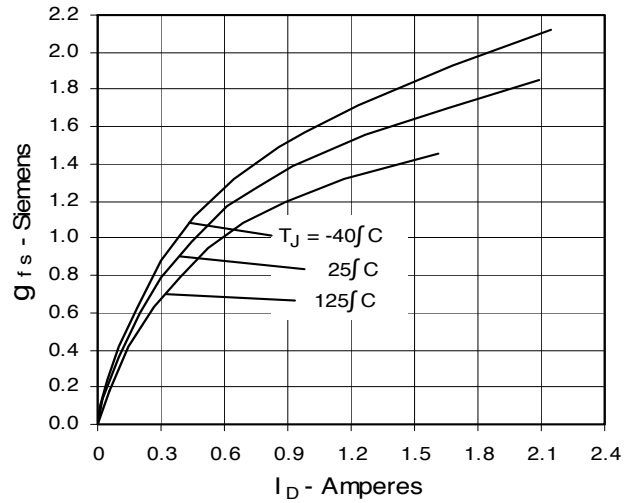
**Fig. 6. Drain Current vs. Case Temperature**



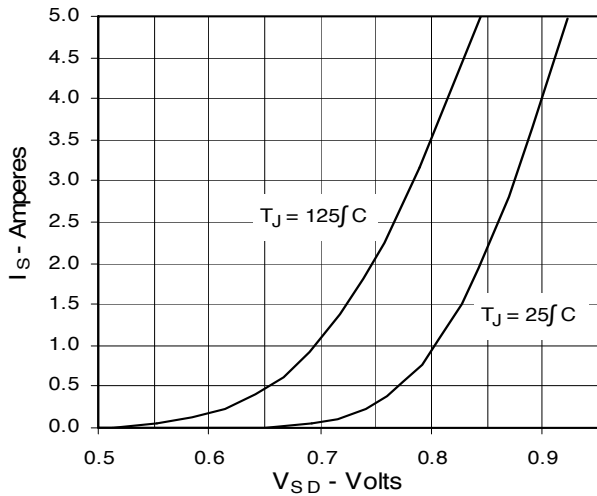
**Fig. 7. Input Admittance**



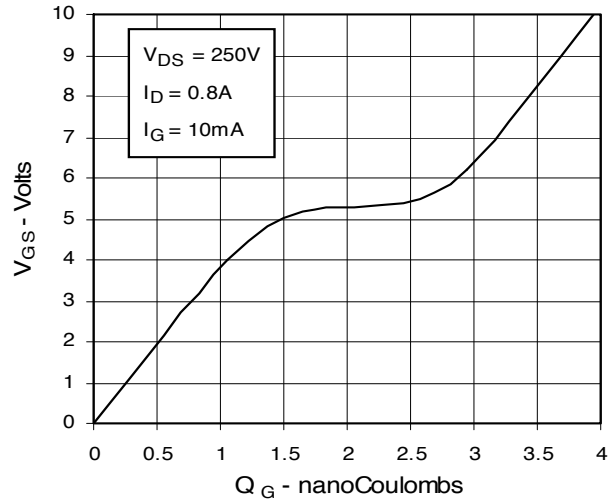
**Fig. 8. Transconductance**



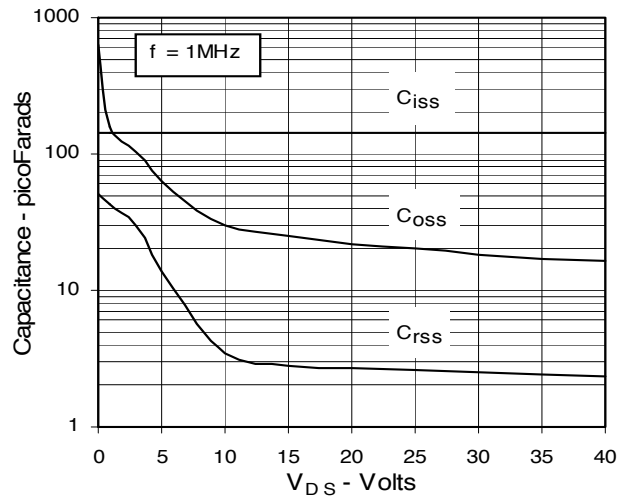
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



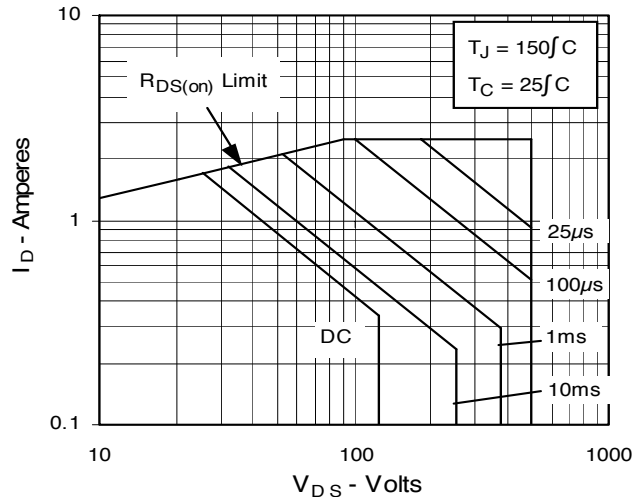
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Forward-Bias Safe Operating Area**



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